PMR3406 - Aula 08/06/2020

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Carga resistiva 5V/60A

PIC: I_{OH}, I_{OL} < 25mA

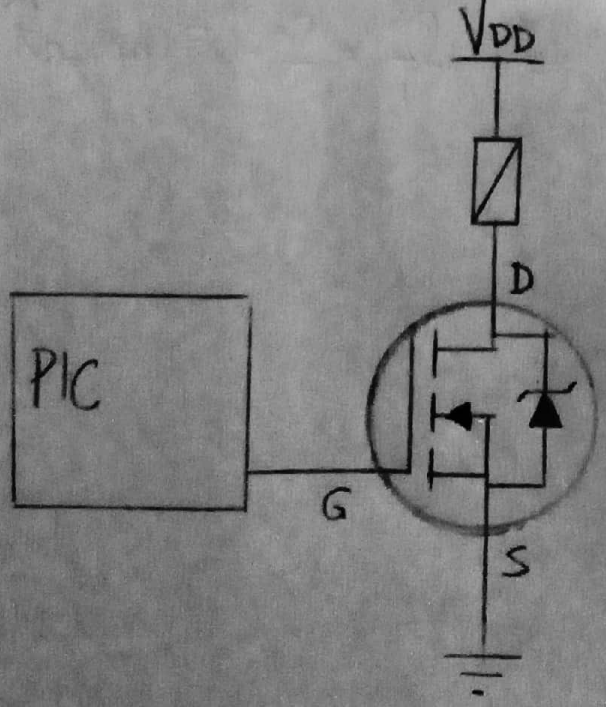
$V_{OL} = [0; 0,6]V$ $V_{OH} = [4,3 ; 5]V$

↳ Considerando GND=0V e V_{DD}=5V

MOSFET escolhido: NCE2060K

↳ N-channel enhancement

$I_D = 60A$, $V_{DS} = 20V$, $V_{GS} = \pm 12V$ $R_{DS(ON)} = 6m\Omega$



Potência: $R_{DS(ON)} . I_D^2 = 0,006 \ 60^2 = 21,6 W$

17.5 DC Characteristics: PIC16F882/883/884/886/887-I (Industrial) PIC16F882/883/884/886/887-E (Extended)

DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating temperature -40°C ≤ TA ≤ +85°C for industrial -40°C ≤ TA ≤ +125°C for extended				
Param No.	**Sym.**	**Characteristic**	**Min.**	**Typ†**	**Max.**	**Units**	**Conditions**
	VIL	**Input Low Voltage**					
		I/O Port:					
D030		with TTL buffer	Vss	—	0.8	V	4.5V ≤ VDD ≤ 5.5V
D030A			Vss	—	0.15 VDD	V	2.0V ≤ VDD ≤ 4.5V
D031		with Schmitt Trigger buffer	Vss	—	0.2 VDD	V	2.0V ≤ VDD ≤ 5.5V
D032		$\overline{MCLR}$, OSC1 (RC mode)(1)	Vss	—	0.2 VDD	V	
D033		OSC1 (XT and LP modes)	Vss	—	0.3	V	
D033A		OSC1 (HS mode)	Vss	—	0.3 VDD	V	
	VIH	Input High Voltage					
		I/O ports:		—			
D040		with TTL buffer	2.0	—	VDD	V	4.5V ≤ VDD ≤ 5.5V
D040A			0.25 VDD + 0.8	—	VDD	V	2.0V ≤ VDD ≤ 4.5V
D041		with Schmitt Trigger buffer	0.8 VDD	—	VDD	V	2.0V ≤ VDD ≤ 5.5V
D042		$\overline{MCLR}$	0.8 VDD	—	VDD	V	
D043		OSC1 (XT and LP modes)	1.6	—	VDD	V	
D043A		OSC1 (HS mode)	0.7 VDD	—	VDD	V	
D043B		OSC1 (RC mode)	0.9 VDD	—	VDD	V	**(Note 1)**
	IIL	Input Leakage Current(2)					
D060		I/O ports	—	± 0.1	± 1	µA	VSS ≤ VPIN ≤ VDD, Pin at high-impedance
D061		$\overline{MCLR}$(3)	—	± 0.1	± 5	µA	VSS ≤ VPIN ≤ VDD
D063		OSC1	—	± 0.1	± 5	µA	VSS ≤ VPIN ≤ VDD, XT, HS and LP oscillator configuration
D070*	IPUR	PORTB Weak Pull-up Current	50	250	400	µA	VDD = 5.0V, VPIN = VSS
	VOL	Output Low Voltage(5)					
D080		I/O ports	—	—	0.6	V	IOL = 8.5 mA, VDD = 4.5V (Ind.)
	VOH	Output High Voltage(5)					
D090		I/O ports	VDD – 0.7	—	—	V	IOH = -3.0 mA, VDD = 4.5V (Ind.)

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: In RC oscillator configuration, the OSC1/CLKIN pin is a Schmitt Trigger input. It is not recommended to use an external clock in RC mode.

2: Negative current is defined as current sourced by the pin.

3: The leakage current on the $\overline{MCLR}$ pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltages.

4: See **Section 10.3.1 "Using the Data EEPROM"** for additional information.

5: Including OSC2 in CLKOUT mode.

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE2060K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

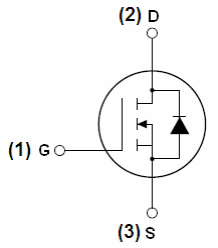
- V_{DS} =20V,I_D =60A
  $R_{DS(ON)}$ <6mΩ @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

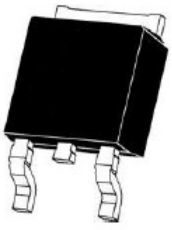
100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram

Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE2060K	NCE2060K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	60	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	42	A
Pulsed Drain Current	I_{DM}	210	A
Maximum Power Dissipation	P_D	60	W
Derating factor		0.48	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	2.1	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.5	0.75	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=20 A	-	4.8	6	mΩ
		V_{GS}=2.5V, I_D=15A		6.2	9	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	2000	-	PF
Output Capacitance	C_{oss}		-	500	-	PF
Reverse Transfer Capacitance	C_{rss}		-	200	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=2A,R_L=1Ω V_{GS}=4.5V,R_G=3Ω	-	6.4	-	nS
Turn-on Rise Time	t_r		-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29.6	-	nS
Turn-Off Fall Time	t_f		-	16.8	-	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=20A, V_{GS}=10V	-	27		nC
Gate-Source Charge	Q_{gs}		-	6.5		nC
Gate-Drain Charge	Q_{gd}		-	6.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	60	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 20A di/dt = 100A/μs (Note3)	-	25	-	nS
Reverse Recovery Charge	Qrr		-	24	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : Tj=25℃,V_{DD}=10V,V_G=10V,L=0.5mH,Rg=25Ω，